Supporting Information

Improved Resistive Switching Characteristics of multi-stacked $HfO_2/Al_2O_3/HfO_2$ RRAM structure for neuromorphic and synaptic applications: Experimental and Computational study

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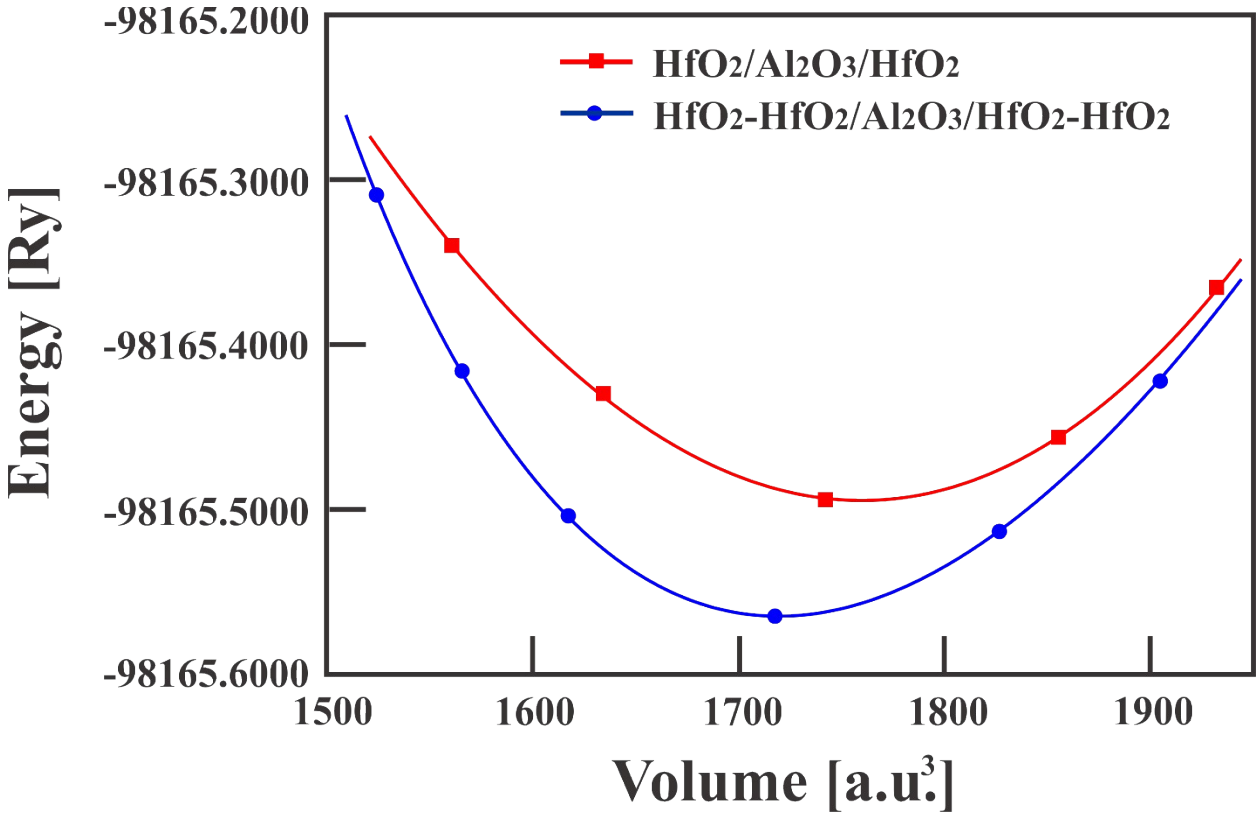

Figure S1. The geometry optimized Energy vs. Volume plots using Birch Murnaghan equation of states.

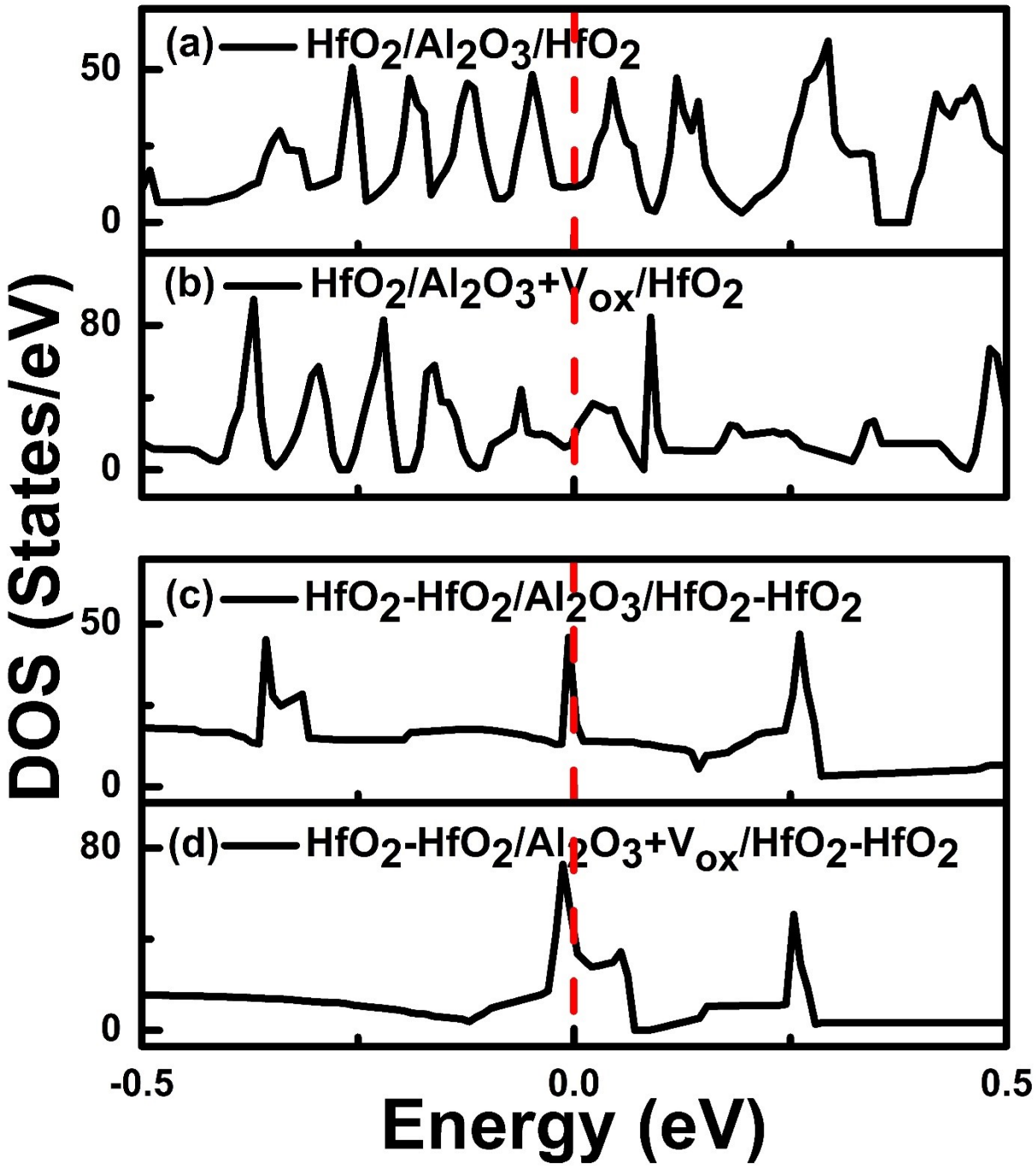

Figure S2. The calculated Density of States (DOS) using VASP simulation code.